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June 2014

FQA70N15 N-Channel QFET® MOSFET

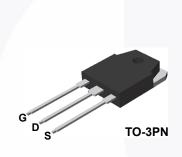
150 V, 70 A, 28 mΩ

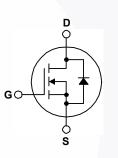
Description

This N-Channel enhancement mode power MOSFET is produced Fairchild using Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched • 175°C Maximum Junction Temperature Rating mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- FQA70N15 N-Channel QFET[®] MOSFET • 70 A, 100 V, $R_{DS(on)}$ = 28 m Ω (Max)@V_{GS} = 10 V, I_D = 35 A
- Low Gate Charge (Typ. 135 nC)
- Low Crss (Typ.135 pF)
- 100% Avalanche Tested





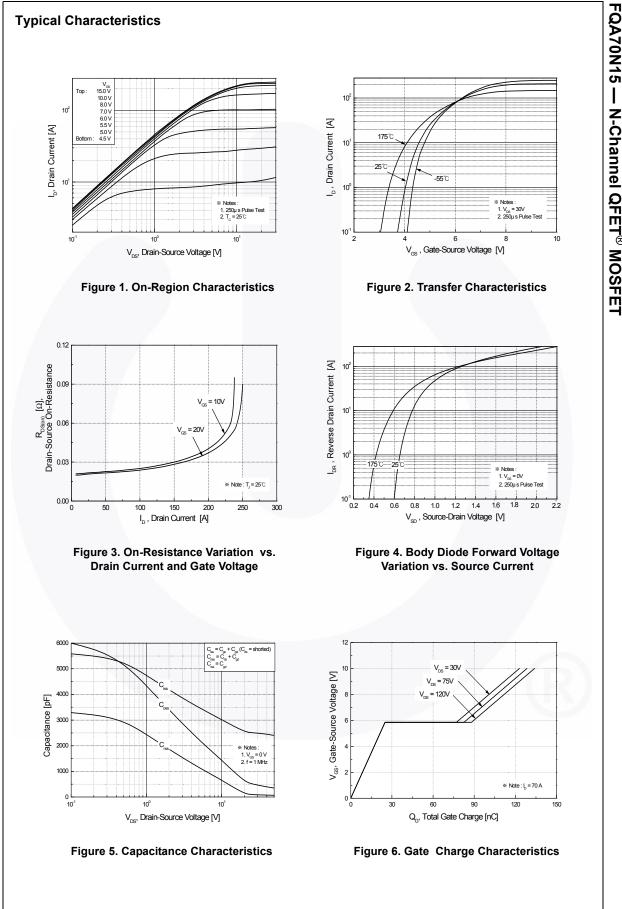
Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FQA70N15	Unit
V _{DSS}	Drain-Source Voltage		150	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$)		70	A
			50	A
I _{DM}	Drain Curent - Pulsed	(Note 1)	280	A
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1000	mJ
I _{AR}	Avalanche Current	(Note 1)	70	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	33	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C		330	W
			2.2	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
ΤL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

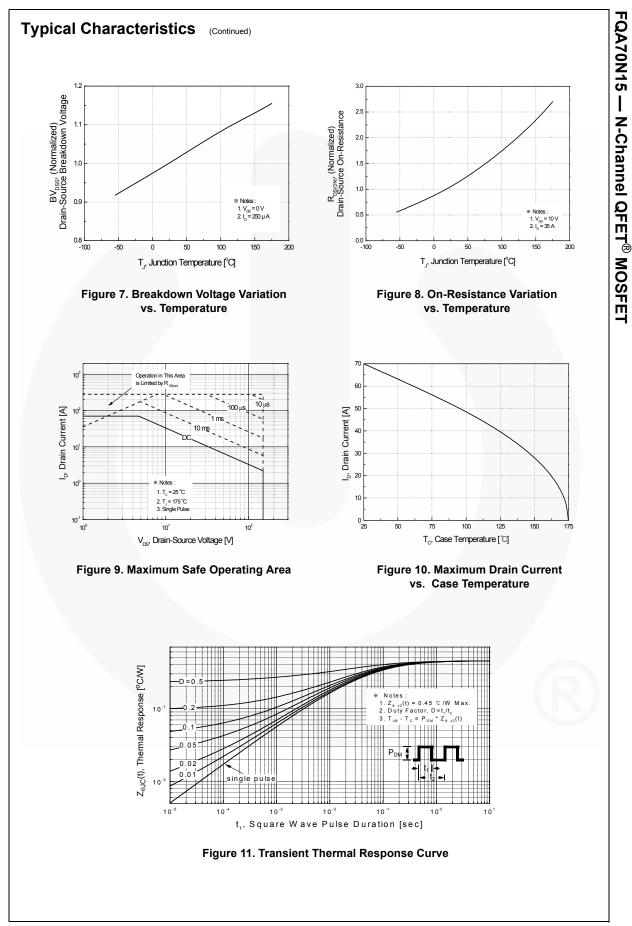
Thermal Characteristics

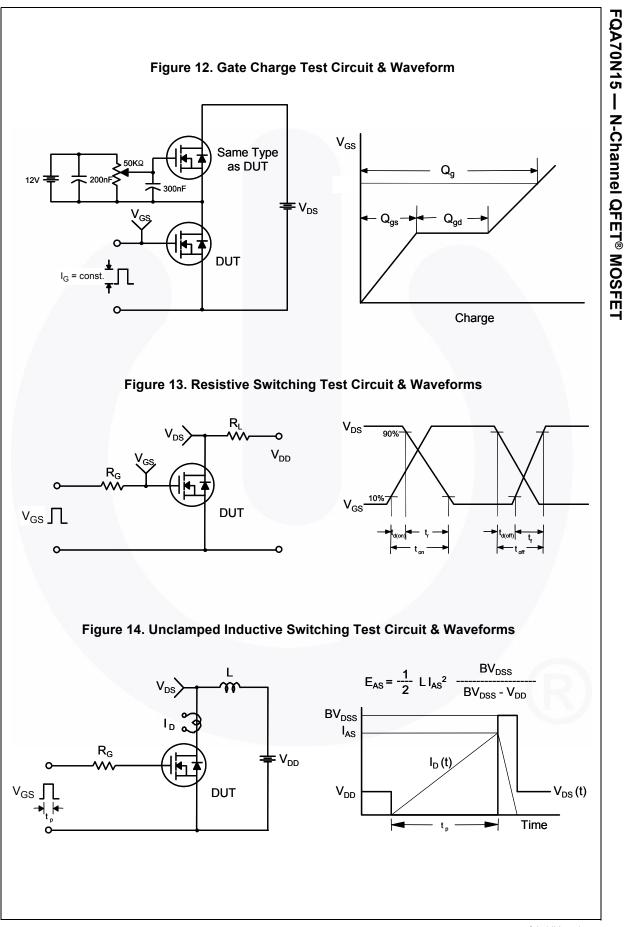
Symbol	Parameter	FQA70N15	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.45	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W

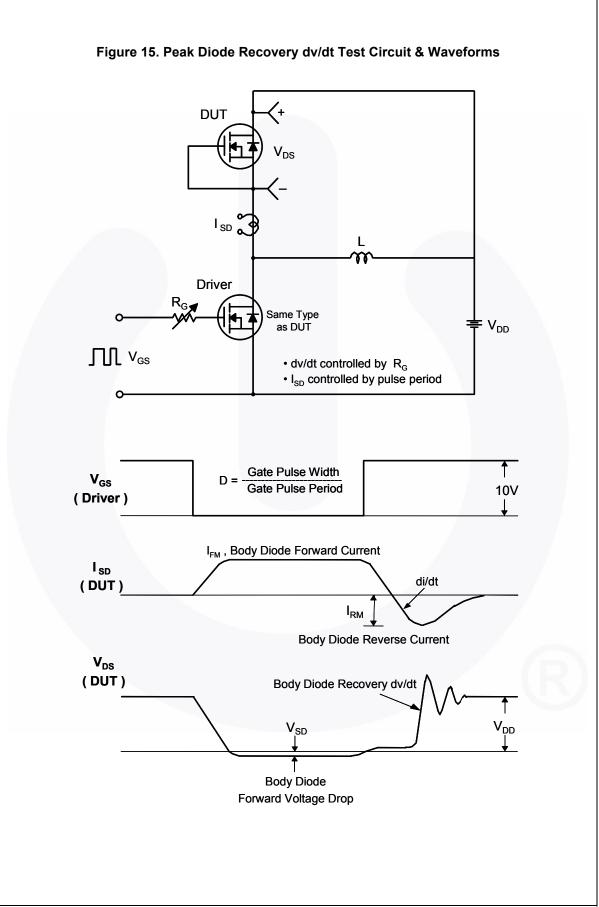
Symbol Off Cha	70N15		Package Reel	Size		Tape Width		Quantity	
Symbol Off Cha ^{BV_{DSS}}		FQA70N15	TO-3PN -			-		30	
Symbol Off Cha ^{BV_{DSS}}	raitinar	acteristics T _c = 25°C	cunless otherwise noted						
		Parameter	Test Conditions		Min	Тур	Max	Unit	
BV _{DSS}				1			1		
			V _{GS} = 0 V, I _D = 250 μA		150			V	
ABVRAA	Drain-Source Breakdown Voltage Breakdown Voltage Temperature				150			v	
ΔBV_{DSS} Breakdown Voltage Ter / ΔT_{J} Coefficient		voltage remperature	$I_D = 250 \mu\text{A}$, Referenced to 25°C			0.15		V/°C	
I _{DSS}	7 0t.	/alta an Daria Ormant	V _{DS} = 150 V, V _{GS} = 0 V				1	μA	
	Zero Gate V	Voltage Drain Current	V _{DS} = 120 V, T _C = 150°C				10	μA	
I _{GSSF}	Gate-Body Leakage Current, Forward		$V_{GS} = 25 V, V_{DS} = 0 V$				100	nA	
I _{GSSR}	Gate-Body	Leakage Current, Reverse	V_{GS} = -25 V, V_{DS} = 0 V				-100	nA	
	racteristic				0.0		10	N	
V _{GS(th)}		hold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$		2.0		4.0	V	
R _{DS(on)}	Static Drain On-Resista		V_{GS} = 10 V, I _D = 35 A			0.023	0.028	Ω	
9 _{FS}	Forward Tra	ansconductance	V _{DS} = 40 V, I _D = 35 A			48		S	
		7				1			
Dynami	c Charact		1			1	r	_	
C _{iss}	Input Capad		V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz			4150	5400	pF	
$\hat{\mathbf{C}}$	Output Cap	acitance				840	1100	pF	
				-					
C _{oss} C _{rss}	Reverse Tra	ansfer Capacitance				135	175	pF	
C _{rss}						135	175		
c _{rss} Switchi	ng Charao	cteristics				<u> </u>	[pF	
C _{rss} Switchi t _{d(on)}	ng Chara Turn-On De	cteristics elay Time	V _{DD} = 75 V, I _D = 70 A,			60	130	pF ns	
C _{rss} Switchi t _{d(on)} t _r	ng Charao Turn-On De Turn-On Ris	cteristics elay Time se Time	V _{DD} = 75 V, I _D = 70 A, R _G = 25 Ω			60 420	130 850	pF ns ns	
$\frac{C_{rss}}{Switchi}$ $\frac{t_{d(on)}}{t_r}$ $t_{d(off)}$	ng Chara Turn-On De Turn-On Ris Turn-Off De	cteristics elay Time se Time elay Time	$R_{G} = 25 \Omega$			60 420 340	130 850 690	pF ns ns ns	
C _{rss} Switchi t _{d(on)} t _r t _{d(off)} t _f	ng Charao Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa	cteristics elay Time se Time elay Time ull Time	R _G = 25 Ω (N	lote 4)	 	60 420 340 290	130 850 690 590	pF ns ns ns ns	
C _{rss} Switchi t _{d(on)} t _r t _{d(off)} t _f Q _g	ng Charao Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate (cteristics elay Time se Time elay Time elay Time Charge	$R_{G} = 25 \Omega$ (N V _{DS} = 120 V, I _D = 70 A,	lote 4)		60 420 340 290 135	130 850 690 590 175	PF ns ns ns ns nC	
$\frac{C_{rss}}{Switchi}$ $\frac{t_{d(on)}}{t_r}$ $\frac{t_{d(off)}}{t_f}$ Q_g Q_{gs}	ng Charac Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate C Gate-Sourc	cteristics elay Time se Time elay Time elay Time ull Time Charge se Charge	$R_{G} = 25 \Omega$ (N V _{DS} = 120 V, I _D = 70 A, V _{GS} = 10 V		 	60 420 340 290 135 25	130 850 690 590	ns ns ns ns nC nC	
C _{rss} Switchi t _{d(on)} t _r t _{d(off)} t _f Q _g	ng Charao Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate (cteristics elay Time se Time elay Time elay Time ull Time Charge se Charge	$R_{G} = 25 \Omega$ (N V _{DS} = 120 V, I _D = 70 A, V _{GS} = 10 V	lote 4)	 	60 420 340 290 135	130 850 690 590 175	PF ns ns ns ns nC	
C _{rss} Switchi t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd}	ng Charao Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate O Gate-Sourc Gate-Drain	cteristics elay Time se Time elay Time elay Time Ull Time Charge charge Charge	$R_{G} = 25 \Omega$ (N V _{DS} = 120 V, I _D = 70 A, V _{GS} = 10 V (N		 	60 420 340 290 135 25	130 850 690 590 175 	ns ns ns ns nC nC	
$\frac{C_{rss}}{Switchi}$ $\frac{Switchi}{t_{d(on)}}$ $\frac{t_{d(off)}}{t_{f}}$ $\frac{C_{gg}}{Q_{gg}}$ Q_{gd} Drain-S	ng Charao Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate (Gate-Sourc Gate-Drain	cteristics elay Time se Time elay Time elay Time dull Time Charge charge Charge charge	$R_{G} = 25 \Omega$ (N) $V_{DS} = 120 V, I_{D} = 70 A,$ $V_{GS} = 10 V$ (N) The Maximum Ratings		 	60 420 340 290 135 25 65	130 850 690 590 175 	pF ns ns ns nC nC nC	
$\begin{array}{c} C_{rss} \\ \hline \textbf{Switchi} \\ t_{d(on)} \\ t_r \\ t_{d(off)} \\ t_f \\ Q_g \\ Q_{gs} \\ Q_{gd} \\ \hline \textbf{Drain-S} \\ I_S \\ \end{array}$	ng Charac Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate C Gate-Sourc Gate-Drain ource Dio Maximum C	cteristics elay Time se Time elay Time elay Time Charge ce Charge Charge charge charge charge	$R_{G} = 25 \Omega$ (N) $V_{DS} = 120 \text{ V}, I_{D} = 70 \text{ A},$ $V_{GS} = 10 \text{ V}$ (N)		 	60 420 340 290 135 25 65	130 850 690 175 70	PF ns ns ns nC nC nC A	
C _{rss} Switchi t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S I _S I _{SM}	ng Charac Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate C Gate-Sourc Gate-Drain Ource Dio Maximum C Maximum F	cteristics elay Time se Time elay Time elay Time dill Time Charge charge Charge Charge Charge ode Characteristics ar Continuous Drain-Source Diode F	$R_{G} = 25 \Omega$ (N) $V_{DS} = 120 \text{ V}, I_{D} = 70 \text{ A},$ $V_{GS} = 10 \text{ V}$ (N)		 	60 420 340 290 135 25 65	130 850 690 590 175 70 280	PF ns ns ns nC nC nC A A	
$\begin{array}{c} C_{rss} \\ \hline \textbf{Switchi} \\ \hline \textbf{t}_{d(on)} \\ \hline \textbf{t}_{r} \\ \hline \textbf{t}_{d(off)} \\ \hline \textbf{t}_{f} \\ Q_{g} \\ Q_{gg} \\ \hline \textbf{Q}_{gg} \\ \hline \textbf{Drain-S} \\ \hline \textbf{I}_{S} \\ \hline \textbf{I}_{SM} \\ \hline \textbf{V}_{SD} \\ \end{array}$	ng Charac Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate O Gate-Sourc Gate-Drain Ource Dio Maximum C Maximum F Drain-Sourc	cteristics elay Time se Time elay Time flage charge charge ode Characteristics and Continuous Drain-Source Diode Pulsed Drain-Source Diode F ce Diode Forward Voltage	$R_{G} = 25 \Omega$ (N) $V_{DS} = 120 V, I_{D} = 70 A,$ $V_{GS} = 10 V$ (N)		 	60 420 340 290 135 25 65 	130 850 690 175 70 280 1.5	PF ns ns ns nC nC nC A A A V	
C _{rss} Switchi t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd} Drain-S I _S I _{SM}	ng Charae Turn-On De Turn-On Ris Turn-Off De Turn-Off Fa Total Gate (Gate-Sourc Gate-Drain Ource Dio Maximum C Maximum F Drain-Sourc Reverse Re	cteristics elay Time se Time elay Time elay Time dill Time Charge charge Charge Charge Charge ode Characteristics ar Continuous Drain-Source Diode F	$R_{G} = 25 \Omega$ (N) $V_{DS} = 120 \text{ V}, I_{D} = 70 \text{ A},$ $V_{GS} = 10 \text{ V}$ (N)		 	60 420 340 290 135 25 65	130 850 690 590 175 70 280	PF ns ns ns nC nC nC A A	

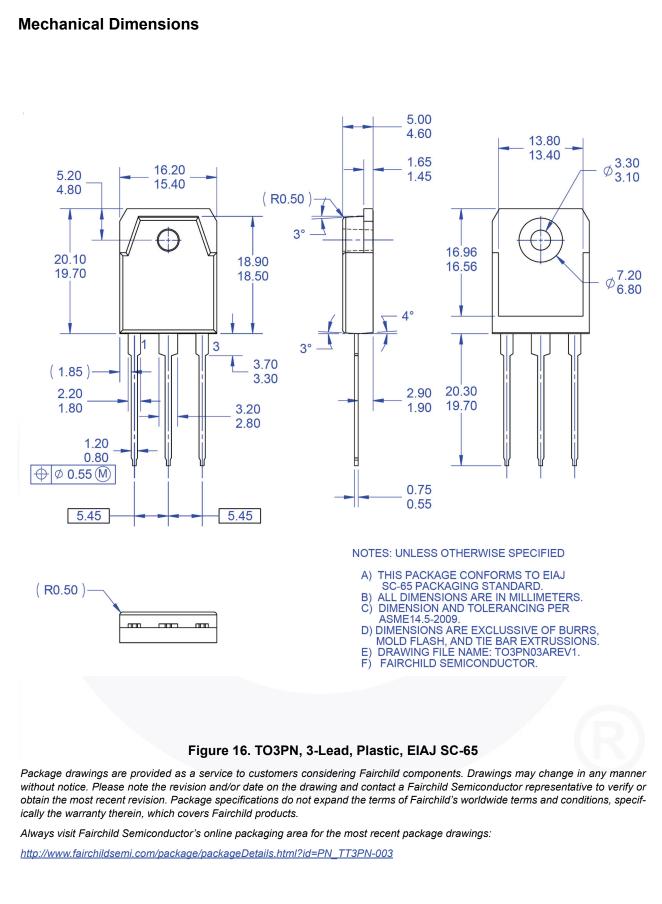


FQA70N15 — N-Channel QFET[®] MOSFET











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